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MOSFET – Power, Single, N-Channel
30 V, 140 A

NVTYS002N03CL

Features

- Low $R_{DS(on)}$ to Minimize Conduction Losses
- Low Capacitance to Minimize Driver Losses
- Optimized Gate Charge to Minimize Switching Losses
- AEC−Q101 Qualified and PPAP Capable
- These Devices are Pb−Free and are RoHS Compliant

MAXIMUM RATINGS (T_J = 25°C unless otherwise stated)

Parameter			Symbol	Value	Unit
Drain−to−Source Voltage			V_{DSS}	30	V
Gate−to−Source Voltage			V_{GS}	±20	V
Continuous Drain Current $R_{\theta JA}$	Steady State	T_A = 25°C	I_D	29	A
		T_A = 100°C		20.5	
Power Dissipation $R_{\theta JA}$		T_A = 25°C	P_D	3.2	W
		T_A = 100°C		1.6	
Continuous Drain Current $R_{\theta JC}$		T_C = 25°C	I_D	140	A
		T_C = 100°C		99	
Power Dissipation $R_{\theta JC}$		T_C = 25°C	P_D	75	W
		T_C = 100°C		37	
Pulsed Drain Current	T_A = 25°C, t_p = 10 μs		I_{DM}	675	A
Operating Junction and Storage Temperature Range			T_J, T_{stg}	−55 to +175	°C
Source Current (Body Diode)			I_S	62	A
Single Pulse Drain−to−Source Avalanche Energy (I_L = 10.6 A)			E_{AS}	320	mJ
Lead Temperature for Soldering Purposes (1/8″ from case for 10 s)			T_L	260	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

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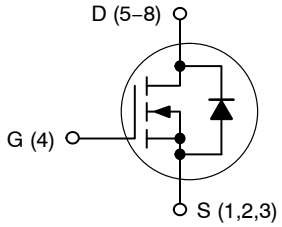
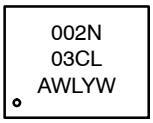
$V_{(BR)DSS}$	$R_{DS(on)}$ MAX	I_D MAX
30 V	2.25 mΩ @ 10 V	140 A
	3.1 mΩ @ 4.5 V	

N−Channel MOSFET



LFPAK8
3.3x3.3
CASE 760AD

MARKING DIAGRAM



002N03CL = Specific Device Code
A = Assembly Location
WL = Wafer Lot
Y = Year
W = Work Week

ORDERING INFORMATION

Device	Package	Shipping†
NVTYS002N03CLTWG	LFPAK33 (Pb−Free)	3000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

THERMAL RESISTANCE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Junction−to−Case (Drain)	$R_{\theta JC}$	2	°C/W
Junction−to−Ambient − Steady State (Note 2)	$R_{\theta JA}$	47	

1. The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.
2. Surface−mounted on FR4 board using a 650 mm^2, 2 oz. Cu pad.
3. Maximum current for pulses as long as 1 second is higher but is dependent on pulse duration and duty cycle.

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise specified)

Parameter	Symbol	Test Condition		Min	Typ	Max	Unit
OFF CHARACTERISTICS							
Drain−to−Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0 V, I_D = 250 μA		30			V
Drain−to−Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS}/T_J$				17.1		mV/°C
Zero Gate Voltage Drain Current	I_{DSS}	V_{GS} = 0 V, V_{DS} = 24 V	T_J = 25°C			1.0	μA
			T_J = 125°C			10	
Zero Gate Voltage Drain Current	I_{DSS}	V_{GS} = 0 V, V_{DS} = 30 V	T_J = 25°C			10	μA
Gate−to−Source Leakage Current	I_{GSS}	V_{DS} = 0 V, V_{GS} = 20 V				100	nA
ON CHARACTERISTICS (Note 4)							
Gate Threshold Voltage	$V_{GS(TH)}$	V_{GS} = V_{DS}, I_D = 250 μA		1.3		2.2	V
Negative Threshold Temperature Coefficient	$V_{GS(TH)}/T_J$				−5.6		mV/°C
Drain−to−Source On Resistance	$R_{DS(on)}$	V_{GS} = 10 V	I_D = 50 A		1.9	2.25	mΩ
		V_{GS} = 4.5 V	I_D = 50 A		2.8	3.1	
Forward Transconductance	g_{FS}	V_{DS} = 1.5 V, I_D = 50 A			130		S
Gate Resistance	R_G				0.9		Ω
CHARGES AND CAPACITANCES							
Input Capacitance	C_{ISS}	V_{GS} = 0 V, f = 1 MHz, V_{DS} = 15 V			2697		pF
Output Capacitance	C_{OSS}				1548		
Reverse Transfer Capacitance	C_{RSS}				43		
Total Gate Charge	$Q_{G(TOT)}$	V_{GS} = 4.5 V, V_{DS} = 15 V; I_D = 50 A			17		nC
Threshold Gate Charge	$Q_{G(TH)}$				3.8		
Gate−to−Source Charge	Q_{GS}				7		
Gate−to−Drain Charge	Q_{GD}				3.8		
Gate Plateau Voltage	V_{GP}				3		V
Total Gate Charge	$Q_{G(TOT)}$	V_{GS} = 10 V, V_{DS} = 15 V; I_D = 50 A			37		nC
SWITCHING CHARACTERISTICS (Note 5)							
Turn−On Delay Time	$t_{d(ON)}$	V_{GS} = 4.5 V, V_{DS} = 15 V, I_D = 50 A, R_G = 3.0 Ω			18		ns
Rise Time	t_r				9		
Turn−Off Delay Time	$t_{d(OFF)}$				22		
Fall Time	t_f				9		

4. Pulse Test: pulse width ≤ 300 μs, duty cycle ≤ 2%.
5. Switching characteristics are independent of operating junction temperatures.

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise specified)

Parameter	Symbol	Test Condition		Min	Typ	Max	Unit
SWITCHING CHARACTERISTICS (Note 5)							
Turn−On Delay Time	$t_{d(ON)}$	V_{GS} = 10 V, V_{DS} = 15 V, I_D = 50 A, R_G = 3.0 Ω			11.5		ns
Rise Time	t_r				4		
Turn−Off Delay Time	$t_{d(OFF)}$				32		
Fall Time	t_f				5		
DRAIN−SOURCE DIODE CHARACTERISTICS							
Forward Diode Voltage	V_{SD}	V_{GS} = 0 V, I_S = 50 A	T_J = 25°C		0.8	1.1	V
			T_J = 125°C		0.7		
Reverse Recovery Time	t_{RR}	V_{GS} = 0 V, dI_S/dt = 100 A/μs, I_S = 50 A			44		ns
Charge Time	t_a				28		
Discharge Time	t_b				13		
Reverse Recovery Charge	Q_{RR}				28		nC

4. Pulse Test: pulse width ≤ 300 μs, duty cycle ≤ 2%.
5. Switching characteristics are independent of operating junction temperatures.

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

TYPICAL CHARACTERISTICS

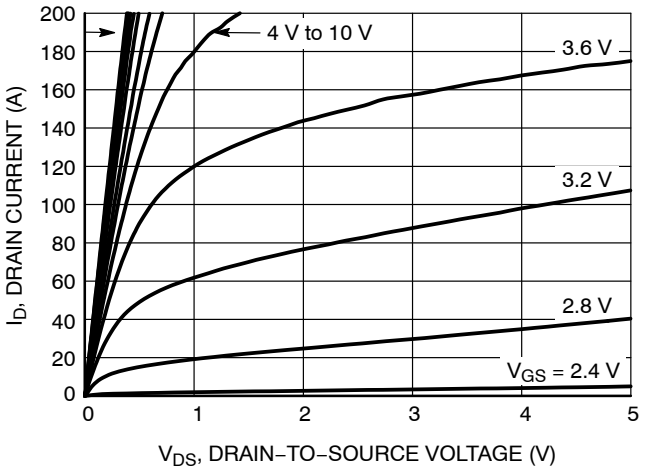


Figure 1. On−Region Characteristics

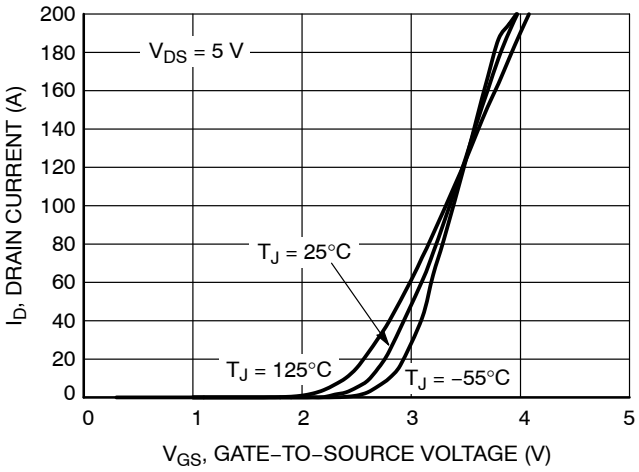


Figure 2. Transfer Characteristics

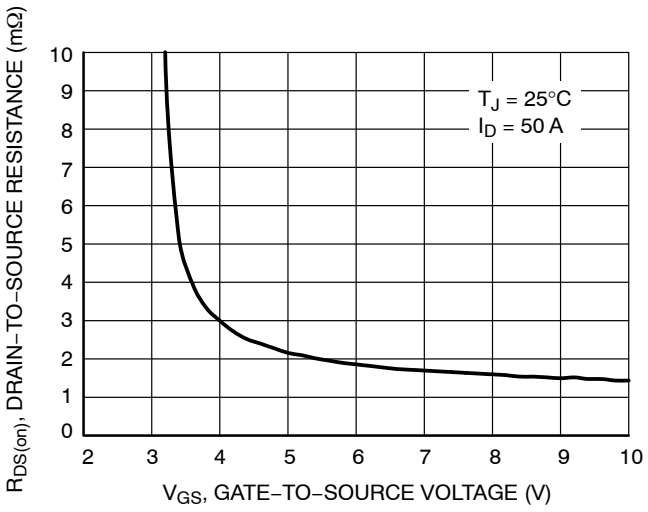


Figure 3. On−Resistance vs. Gate−to−Source Voltage

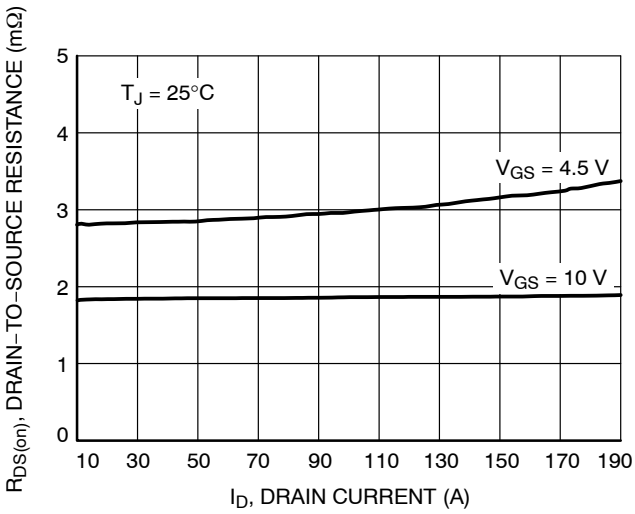


Figure 4. On−Resistance vs. Drain Current and Gate Voltage

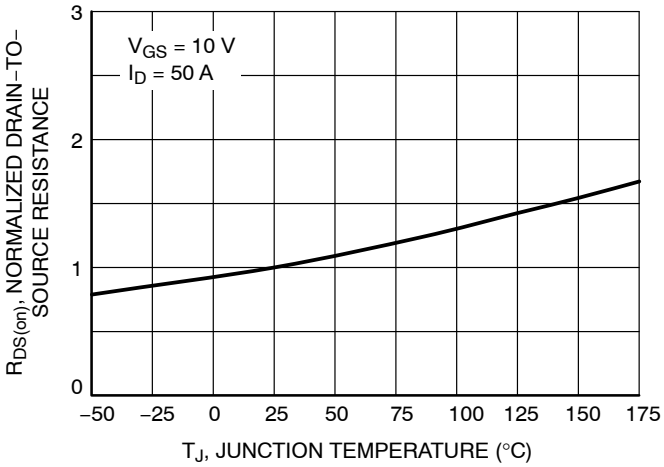


Figure 5. On−Resistance Variation with Temperature

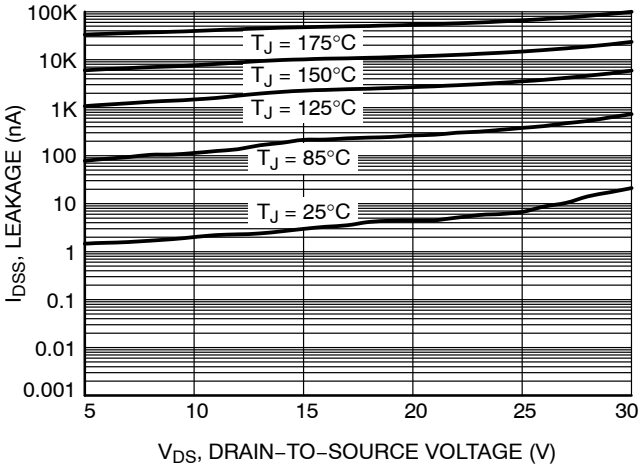


Figure 6. Drain−to−Source Leakage Current vs. Voltage

TYPICAL CHARACTERISTICS

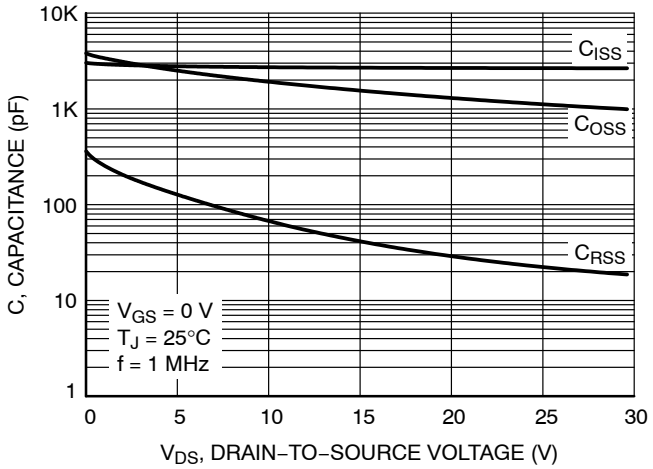


Figure 7. Capacitance Variation

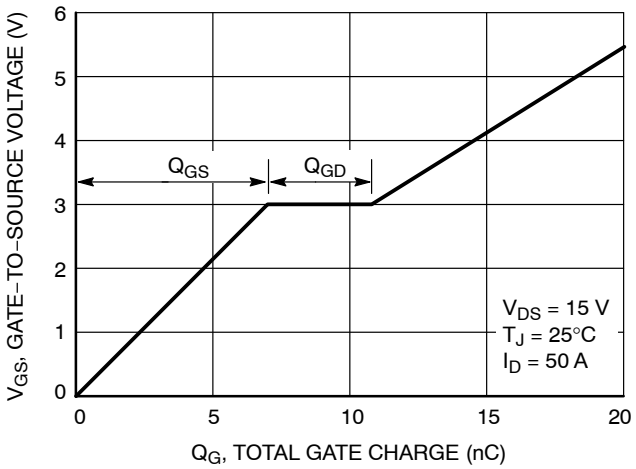


Figure 8. Gate−to−Source vs. Total Charge

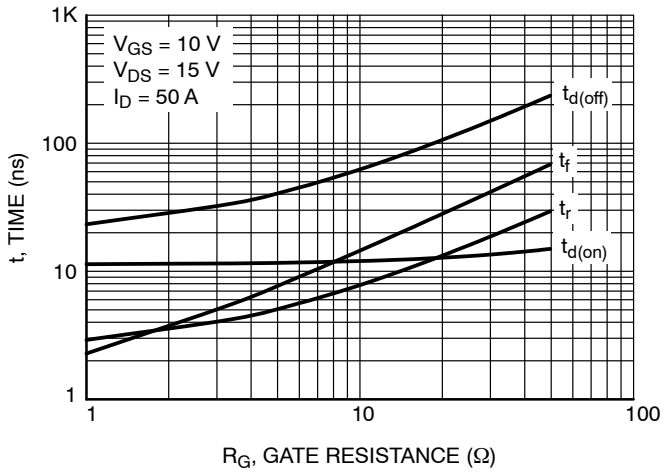


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

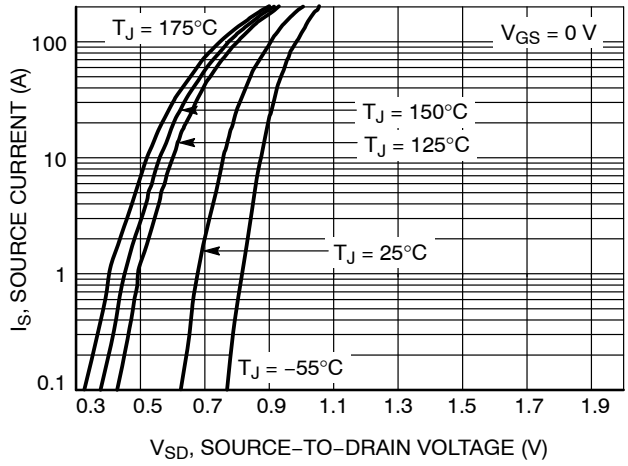


Figure 10. Diode Forward Voltage vs. Current

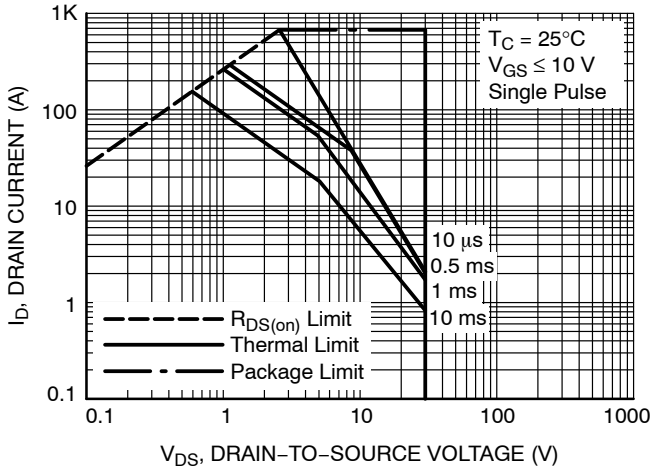


Figure 11. Maximum Rated Forward Biased Safe Operating Area

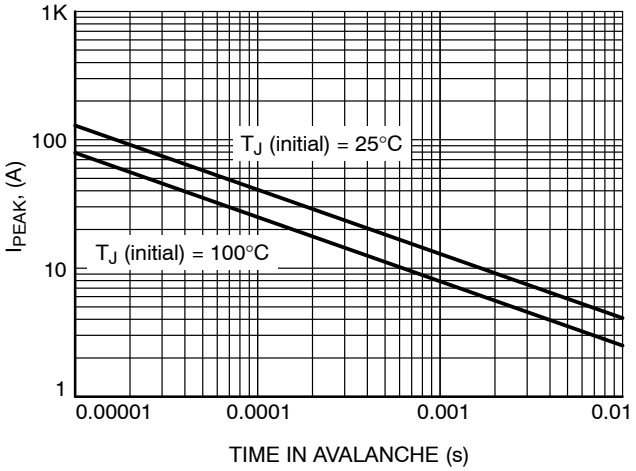


Figure 12. I_{PEAK} vs. Time in Avalanche

TYPICAL CHARACTERISTICS

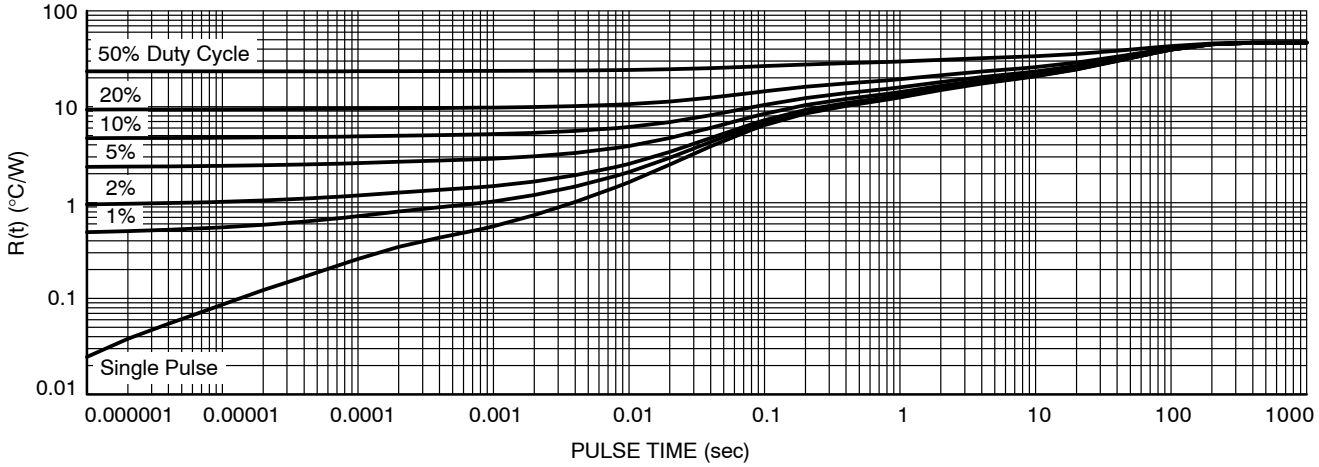
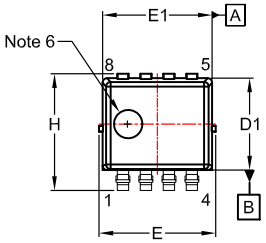


Figure 13. Thermal Characteristics

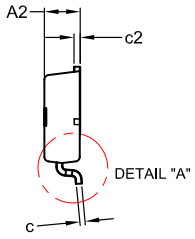
NVTYS002N03CL

PACKAGE DIMENSIONS

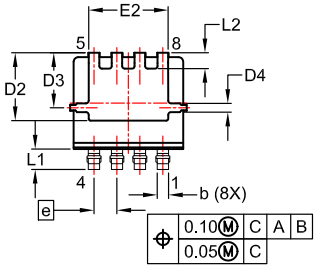
LFPAK8 3.3x3.3, 0.65P
CASE 760AD
ISSUE E



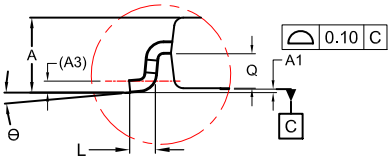
TOP VIEW



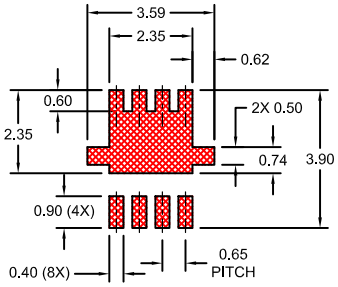
SIDE VIEW



BOTTOM VIEW



DETAIL 'A'
SCALE: 2:1



LAND PATTERN
RECOMMENDATION

*FOR ADDITIONAL INFORMATION ON OUR PB-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS
3. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR BURRS. MOLD FLASH, PROTRUSIONS OR BURRS SHALL NOT EXCEED 0.150mm PER SIDE.
4. DIMENSIONS D AND E ARE DETERMINED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
5. DATUMS A AND B ARE DETERMINED AT DATUM PLANE H.
6. OPTIONAL MOLD FEATURE.

DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	0.95	1.05	1.15
A1	0.00	0.05	0.10
A2	0.95	1.00	1.05
A3		0.15 REF	
b	0.27	0.32	0.37
c	0.12	0.17	0.22
c2	0.12	0.17	0.22
D1	2.50	2.60	2.70
D2	1.82	1.92	2.02
D3	1.46	1.56	1.66
D4	0.20	0.25	0.30
E	3.20	3.30	3.40
E1	3.00	3.10	3.20
E2	2.15	2.25	2.35
e		0.65 BSC	
H	3.20	3.30	3.40
L	0.25	0.37	0.50
L1	0.48	0.58	0.68
L2	0.35	0.45	0.55
Q	0.45	0.50	0.55
θ	0°	4°	8°

PUBLICATION ORDERING INFORMATION

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